

ROH-051

PCT SECTION

9.

(Amended) A semiconductor device as set forth in any of claims 1 to 4, wherein a bonding region is defined on the first conductivity type semiconductor region for bonding a wire to the electrode, and the diode is provided at least in a part of the boundary portion of the contact region adjacent to the bonding region.

10.

(Amended) A semiconductor device as set forth in any of claims 1 to 4, wherein the functional element is a bipolar transistor which comprises a base region defined by the first conductivity type semiconductor region, and an emitter region defined by the second conductivity type semiconductor region.--

REMARKS

This Preliminary Amendment is requested prior to the initial examination of the above-identified patent application to eliminate multiple dependency. If the Examiner has any suggestions for placing this application in even better form, the Examiner is invited to telephone the undersigned and the number listed below.

Respectfully submitted,



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Date: March 7, 2002

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Appendix

In accordance with 37 CFR 1.121(b)(1)(iii), the amended paragraphs are set forth in a marked-up version below:

IN THE CLAIMS:

Claims 6-10 have been amended as follows:

6. A semiconductor device as set forth in any of claims 1 to [5]4, wherein the contact region has a generally C-shape or a ring shape which surrounds the second conductivity type semiconductor region on the surface of the first conductivity type semiconductor region.

7. A semiconductor device as set forth in any of claims 1 to [6]4, wherein the diode is provided at least in a part of the boundary portion of the contact region facing the second conductivity type semiconductor region.

8. A semiconductor device as set forth in any of claims 1 to [6]4, wherein the diode is provided in the entire boundary portion of the contact region.

9. A semiconductor device as set forth in any of claims 1 to [7]4, wherein a bonding region is defined on the first conductivity type semiconductor region for bonding a wire to the electrode, and the diode is provided at least in a part of the boundary portion of the contact region adjacent to the bonding region.

10. A semiconductor device as set forth in any of claims 1 to [9]4, wherein the functional element is a bipolar transistor which comprises a base region defined by the first conductivity type semiconductor region, and an emitter region defined by the second conductivity type semiconductor region.